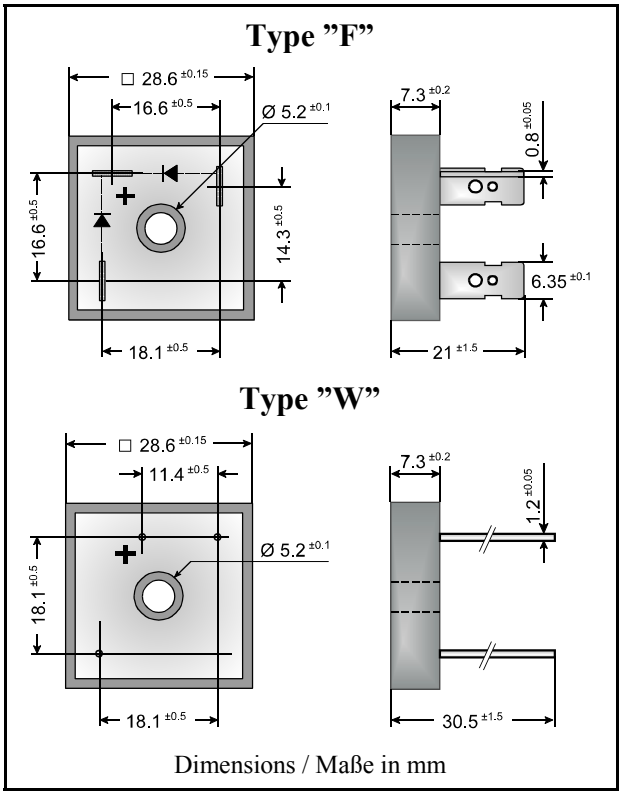
Silicon-Twin Rectifiers
Center tap

Silizium-Doppeldioden
Mittelpunktschaltung



Dimensions / Maße in mm

Nominal current Nennstrom	30 A
Alternating input voltage Eingangswechselspannung	60…250 V
Plastic case with alu-bottom Kunststoffgehäuse mit Alu-Boden	
Dimensions Abmessungen	28.6 x 28.6 x 7.3 [mm]
Weight approx. Gewicht ca.	23 g
Recognized Product – UL-File E175067 Anerkanntes Produkt – UL Nr. E175067	
Compound has classification UL94V-0 Vergußmasse UL94V-0 klassifiziert	
Standard packaging: bulk Standard Lieferform: lose im Karton	see page 22 s.S. 22

Maximum ratings **Grenzwerte**

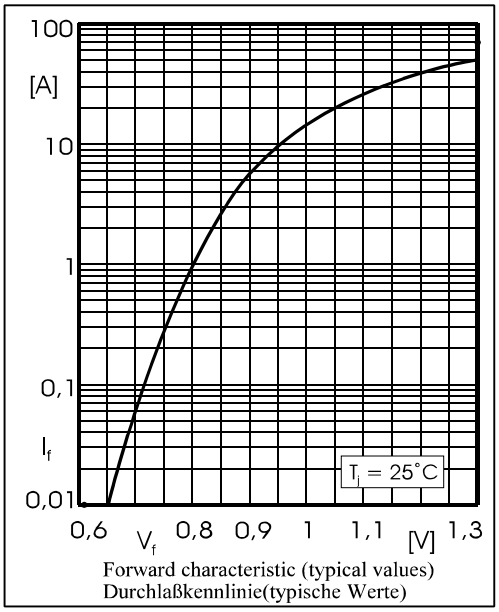
Type Typ	max. alternating input voltage max. Eingangswechselspannung V_{VRMS} [V]	Repetitive peak reverse voltage Periodische Spitzensperrspannung V_{RRM} [V] [1]
D30 VC20 F/W	60	200
D30 VC40 F/W	120	400
D30 VC60 F/W	190	600
D30 VC80 F/W	250	800

Repetitive peak fwd. current – Period. Spitzenstrom	f > 15 Hz	I_{FRM}	80 A [2]
Peak forward surge current, 50 Hz half sine-wave Stoßstrom für eine 50 Hz Sinus-Halbwelle	T_A = 25˚C	I_{FSM}	300 A
Rating for fusing – Grenzlastintegral, t < 10 ms	T_A = 25˚C	i^2t	450 A^2s
Isolation voltage – Isolationsspannung	t = 1 min	V_{ISO}	> 2000 V
Operating junction temperature – Sperrschichttemperatur		T_j	– 50…+150˚C
Storage temperature – Lagerungstemperatur		T_S	– 50…+150˚C

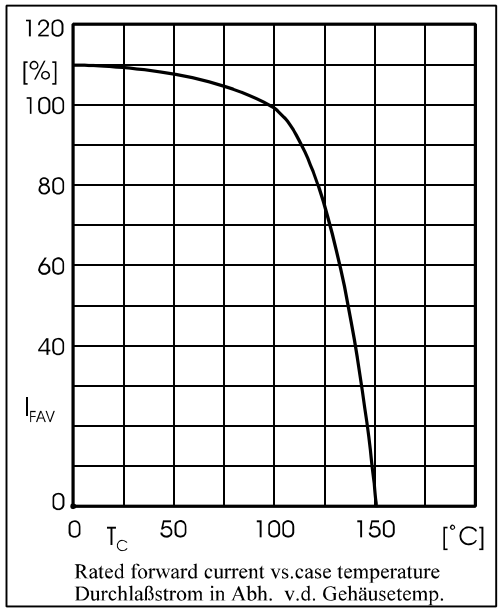
[1]) Valid per diode – Gültig pro Diode
[2]) Max. case temperature T_C = 100˚C – Max. Gehäusetemperatur T_C = 100˚C

Characteristics — Kennwerte

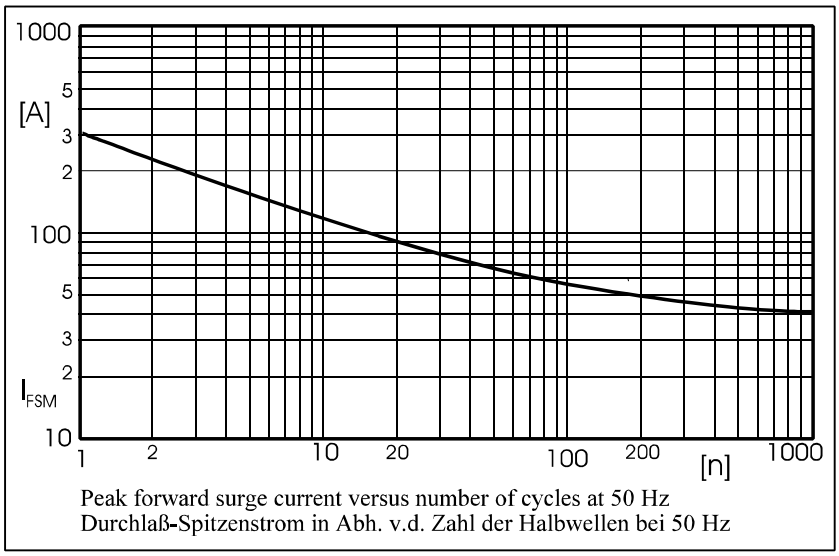
Max. current with cooling fin 300 cm²	$T_A = 50^\circ C$	R-load	I_{FAV}	30.0 A
Dauergrenzstrom mit Kühlblech 300 cm²		C-load	I_{FAV}	26.0 A
Forward voltage – Durchlaßspannung	$T_j = 25^\circ C$	$I_F = 15$ A	V_F	< 1.05 V [1])
Leakage current – Sperrstrom	$T_j = 25^\circ C$	$V_R = V_{RRM}$	I_R	< 25 µA
Thermal resistance junction to case Wärmewiderstand Sperrschicht – Gehäuse			R_{thC}	< 1.0 K/W
Admissible torque for mounting Zulässiges Anzugsdrehmoment		10-32 UNF M 5		18 ± 10% lb.in 2 ± 10% Nm



Forward characteristic (typical values)
Durchlaßkennlinie(typische Werte)



Rated forward current vs.case temperature
Durchlaßstrom in Abh. v.d. Gehäusetemp.



Peak forward surge current versus number of cycles at 50 Hz
Durchlaß-Spitzenstrom in Abh. v.d. Zahl der Halbwellen bei 50 Hz

[1]) Valid per diode – Gültig pro Diode